CMOS Quad Low-to-High Voltage Level Shifter

High-Voltage Types (20-Volt Rating)

The RCA-CD40109B contains four low-to-high-voltage level-shifting circuits. Each circuit will shift a low-voltage digital-logic input signal (A, B, C, D) with logical 1 = V_{CC} and logical 0 = V_{SS} to a higher-voltage output signal (E, F, G, H) with logical 1 = V_{DD} and logical 0 = V_{SS}.

The RCA-CD40109, unlike other low-to-high level-shifting circuits, does not require the presence of the high-voltage supply (V_{DD}) before the application of either the low-voltage supply (V_{CC}) or the input signals. There are no restrictions on the sequence of application of V_{DD}, V_{CC}, or the input signals. In addition, with one exception there are no restrictions on the relative magnitudes of the supply voltages or input signals within the device maximum ratings, provided that the input signal swings between V_{SS} and at least 0.7 V_{CC}; V_{CC} may exceed V_{DD}, and input signals may exceed V_{CC} and V_{DD}. When operated in the mode $V_{CC} > V_{DD}$, the CD40109 will operate as a high-to-low level-shifter.

The CD40109 also features individual three-state output capability. A low level on any of the separately enabled three-state output controls produces a high-impedance state in the corresponding output.

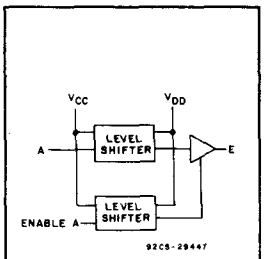
The CD40109B-Series types are supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Applications:

- **High-or-low level-shifting with three-state outputs for unidirectional or bidirectional bussing**
- **Isolation of logic subsystems using separate power supplies from supply sequencing, supply loss and supply regulation considerations**

Features:

- **Independence of power supply sequence considerations—V_{CC} can exceed V_{DD}, input signals can exceed both V_{CC} and V_{DD}**
- **Up and down level-shifting capability**
- **Three-state outputs with separate enable controls**
- **Standardized, symmetrical output characteristics**
- **100% tested for quiescent current at 20 V**
- **Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C**
- **Noise margin (full package-temperature range)**
  = 1 V at V_{CC} = 5 V, V_{DD} = 10 V
  = 2 V at V_{CC} = 10 V, V_{DD} = 15 V
- **5-V, 10-V, and 15-V parametric ratings**
- **Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"**



FUNCTIONAL DIAGRAM (1 of 4 units)

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -40 to +60°C (PACKAGE TYPE E) ..... 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) ..... Derate Linearly at 12 mW/°C to 200 mW
For T_A = -55 to +100°C (PACKAGE TYPES D, F, K) ..... 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K) ..... Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:
For T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H ..... -55 to +125°C
PACKAGE TYPE E ..... -40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. ..... +265°C

TRUTH TABLE

INPUTS		OUTPUTS
A, B, C, D	ENABLE A, B, C, D	E, F, G, H
0	1	0
1	1	1
X	0	Z

LOGIC 0 = LOW(V_{SS}) X = DON'T CARE Z = HIGH IMPEDANCE
LOGIC 1 = V_{CC} at INPUTS and V_{DD} at OUTPUTS

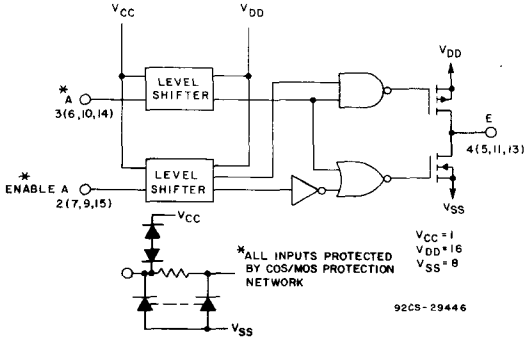


Fig. 1 – CD40109B logic diagram (1 of 4 units).

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at −55, +25, +125 Apply to D, F, K, H Packages Values at −40, +25, +85 Apply to E Package							UNITS
									+25		
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	μA
3-State Output Leakage Current I_{OUT} Max.		0,18	18	±0.4	±0.4	±12	±12	–	$±10^{-4}$	±0.4	μA
	V_O (V)	V_{CC} (V)	V_{DD} (V)								
Input Low Voltage, V_{IL} Max.	1,9	5	10	1.5				—	—	1.5	V
	1.5, 13.5	10	15	3				—	—	3	
Input High Voltage, V_{IH} Min.	1,9	5	10	3.5				3.5	—	—	
	1.5,13.5	10	15	7				7	—	—	

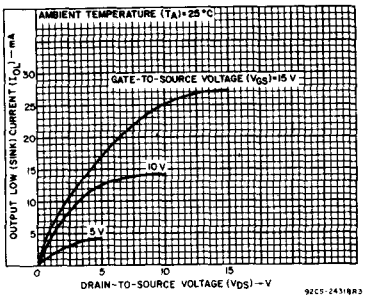


Fig.2 – Typical output low (sink) current characteristics.

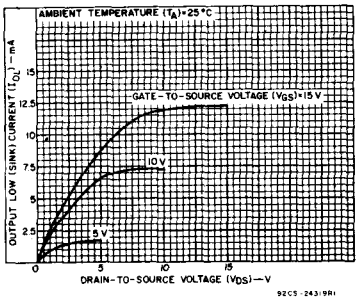


Fig.3 – Minimum output low (sink) current characteristics.

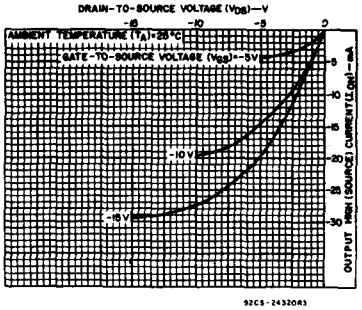


Fig.4 – Typical output high (source).

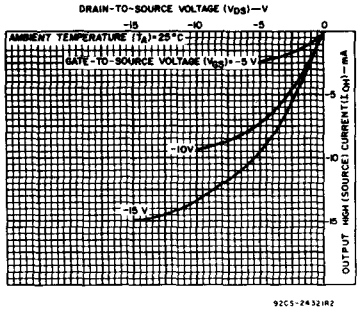


Fig.5 – Minimum output high (source) current characteristics.

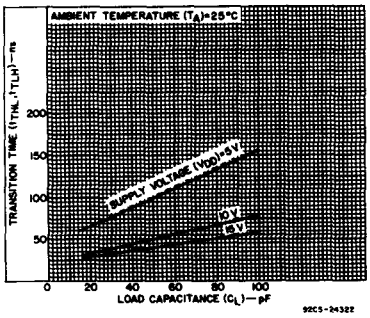


Fig.6 – Typical transition time as a function of load capacitance.

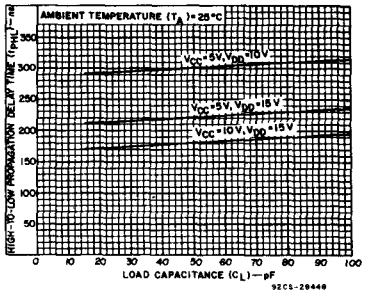


Fig.7 – Typical high-to-low propagation delay time as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ unless otherwise specified

CHARACTERISTIC	SHIFTING MODE	V_{CC} (V)	V_{DD} (V)	LIMITS Typ.	LIMITS Max.	UNITS
Propagation Delay – Data Input to Output: High-to-Low Level, t_{PHL}	L–H	5	10	300	600	ns
		5	15	220	440	
		10	15	180	360	
	H–L	10	5	250	500	
		15	5	250	500	
		15	10	120	240	
Low-to-High Level, t_{PLH}	L–H	5	10	130	260	ns
		5	15	120	240	
		10	15	70	140	
	H–L	10	5	230	460	
		15	5	230	460	
		15	10	80	160	
3-State Disable Delay: R_L = 1 kΩ Output High to High Impedance, t_{PHZ}	L–H	5	10	60	120	ns
		5	15	75	150	
		10	15	35	70	
	H–L	10	5	200	400	
		15	5	200	400	
		15	10	40	80	
Output Low to High Impedance, t_{PLZ}	L–H	5	10	370	740	ns
		5	15	300	600	
		10	15	250	500	
	H–L	10	5	250	500	
		15	5	250	500	
		15	10	130	260	
High Impedance to Output High, t_{PZH}	L–H	5	10	320	640	ns
		5	15	230	460	
		10	15	180	360	
	H–L	10	5	300	600	
		15	5	300	600	
		15	10	130	260	
High Impedance to Output Low, t_{PZL}	L–H	5	10	100	200	ns
		5	15	80	160	
		10	15	40	80	
	H–L	10	5	200	400	
		15	5	200	400	
		15	10	40	80	
Transition Time, t_{THL}, t_{TLH}	L–H	5	10	50	100	ns
		5	15	40	80	
		10	15	40	80	
	H–L	10	5	100	200	
		15	5	100	200	
		15	10	50	100	
Input Capacitance, C_I		Any Input		5	7.5	pF

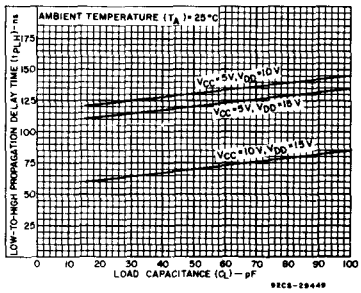


Fig.8 – Typical low-to-high propagation delay time as a function of load capacitance.

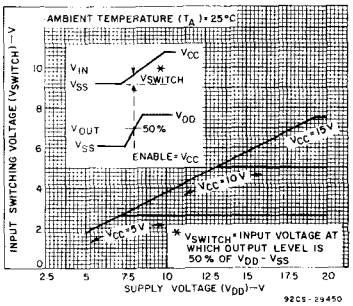


Fig.9 – Typical input switching as a function of high-level supply voltage.

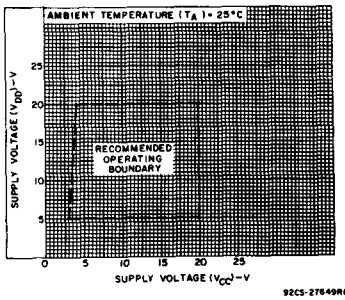


Fig.10 – High-level supply voltage vs. low-level supply voltage.

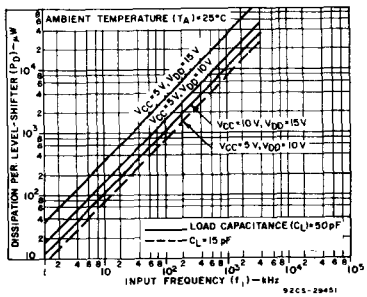


Fig.11 – Typical dynamic power dissipation as a function of input frequency.

TEST CIRCUITS

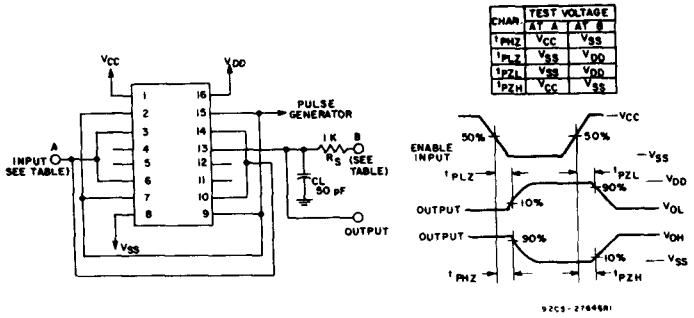


Fig. 12 – Output enable delay times test circuit and waveforms.

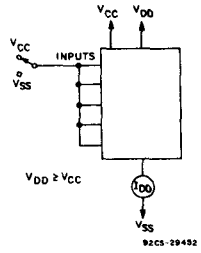


Fig. 13 – Quiescent device current.

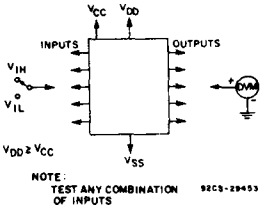


Fig. 14 – Input voltage.

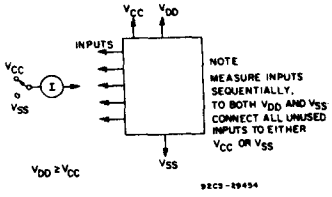


Fig. 15 – input current.

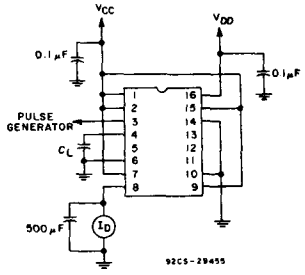
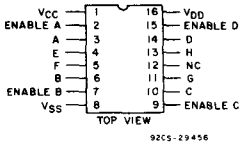


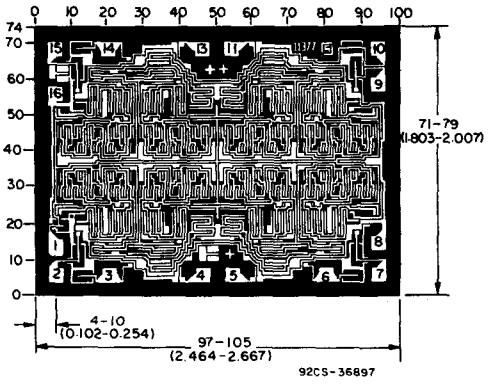
Fig. 16 – Dynamic power dissipation test circuit.



CD40109B
TERMINAL ASSIGNMENT

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.



Dimensions and pad layout for CD40109BH.